

## Product specifications

| Silicon carbide substrate material specification |                 |
|--------------------------------------------------|-----------------|
| Property                                         | Value           |
| Polytype                                         | 4H polytype     |
| Orientation                                      | 4° offcut       |
| Diameter                                         | 200 ±0.05mm     |
| Thickness                                        | 350+/- 10µm     |
| Warp                                             | <25µm           |
| TTV                                              | <4 µm           |
| Surface treatment (Si-face)                      | Epi-ready       |
| Resistivity                                      | 19.5-20.5 mΩ.cm |
| Resistivity uniformity                           | <2%             |
| Edge exclusion                                   | 3 mm            |

| Defect density                            |                         |
|-------------------------------------------|-------------------------|
| Property                                  | Value                   |
| Micropipes (MP)                           | <2 on wafer             |
| Basal plane dislocation density (BPD)     | <70 on wafer            |
| Threading screw dislocation density (TSD) | <100 cm <sup>-2</sup>   |
| Threading edge dislocation density (TED)  | <800 cm <sup>-2</sup>   |
| Etch pit density (EPD)                    | <1'000 cm <sup>-2</sup> |

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